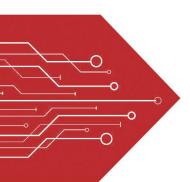
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet







- 1. BASE
- 2. EMITTER

DEVICE MARKING

SOT - 23

3. COLLECTOR

P/N MARK P/N MARK P/N MARK BC856A 3A BC856B 3B BC857C 3E BC857B 3F 3G BC857A BC858C 3L BC858A 3J BC858B 3K

TRANSISTOR (PNP)

FEATURES

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

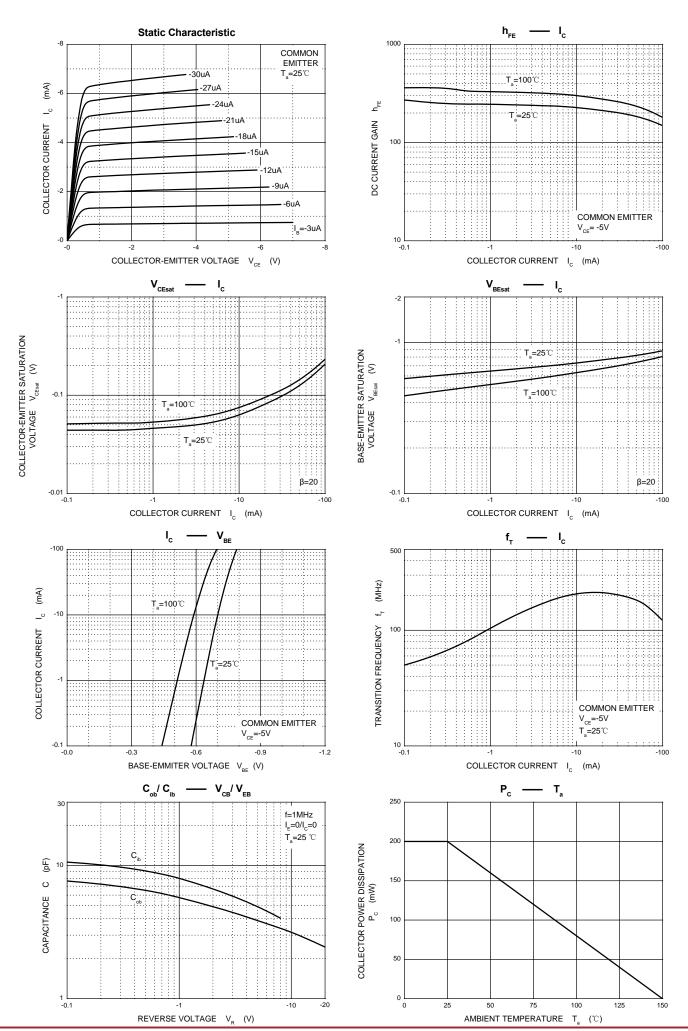
MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage		V	
	BC856	-80		
	BC857	-50	V	
	BC858	-30		
V _{CEO}	Collector-Emitter Voltage			
	BC856	-65	V	
	BC857	-45		
	BC858	-30		
V _{EBO}	Emitter-Base Voltage	-5	V	
lc	Collector Current –Continuous	-0.1	Α	
Pc	Collector Power Dissipation	200	mW	
R _{OJA}	Thermal Resistance From Junction To Ambient	625	°C/W	
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}$	

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

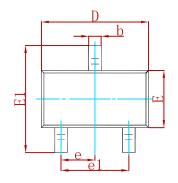
Parameter		Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	BC856			-80		
	BC857	V_{CBO}	I _C = -10μΑ, I _E =0	-50		V
	BC858			-30		
Collector-emitter breakdown voltage	BC856			-65		
	BC857	V_{CEO}	$I_C = -10$ mA, $I_B = 0$	-45		V
	BC858			-30		
Emitter-base breakdown voltage		V_{EBO}	I _E = -1μΑ, I _C =0	-5		V
Collector cut-off current	BC856		V _{CB} = -70 V , I _E =0			
	BC857	I _{CBO}	V_{CB} = -45 V , I_{E} =0		-0.1	μΑ
	BC858		V _{CB} = -25 V , I _E =0			
Emitter cut-off current		I _{EBO}	V_{EB} = -5 V , I_{C} =0		-0.1	μA
DC current gain BC85	6A, 857A,858A			125	250	
BC85	6B, 857B,858B	h_FE	V_{CE} = -5 V , I_{C} = -2 mA	220	475	
В	C857C,BC858C			420	800	
Collector-emitter saturation voltage		$V_{\text{CE}(\text{sat})}$	I_C =-100mA, I_B = -5 mA		-0.5	V
Base-emitter saturation voltage		V _{BE} (sat)	I _C = -100mA, I _B = -5mA		-1.1	V
Transition frequency		f⊤	V_{CE} = -5 V, I_{C} = -10mA f=100MHz	100		MHz
Collector capacitance		C _{ob}	V _{CB} =-10V, f=1MHz		4.5	pF

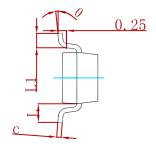


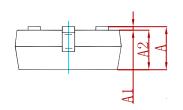




PACKAGE MECHANICAL DATA

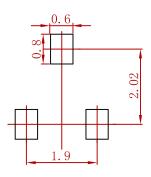






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BC856/57/58ABC	SOT-23	3000



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